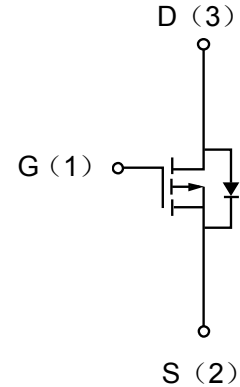


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
-20	0.08 @ V _{GS} =-4.5V	-2.8
	0.11 @ V _{GS} =-2.5V	


Electrical characteristics per line @25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = -250μA, V _{GS} = 0V	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±10V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.45		-0.9	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -2.8A	-	0.08	0.11	Ω
		V _{GS} = -2.5V, I _D = -2.0A	-	0.11	0.15	Ω
Forward Tran conductance	g _{FS}	V _{GS} = 5V, I _D = 50mA, T _A = 125°C		6.5		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	360		pF
Output Capacitance	C _{DSS}		-	125		pF
Reverse Transfer Capacitance	C _{RSS}		-	50		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 6Ω, R _G = 6Ω, I _D = -1A	-		17	ns
Turn-Off Delay Time	t _{d(off)}		-		35	ns

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	V
Drain Current	Continuous	I_D	-2.8	A
	Pulsed	I_D	-8	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	900	mW
	$T_A=125^\circ\text{C}$	P_D	570	mW

Typical Characteristics

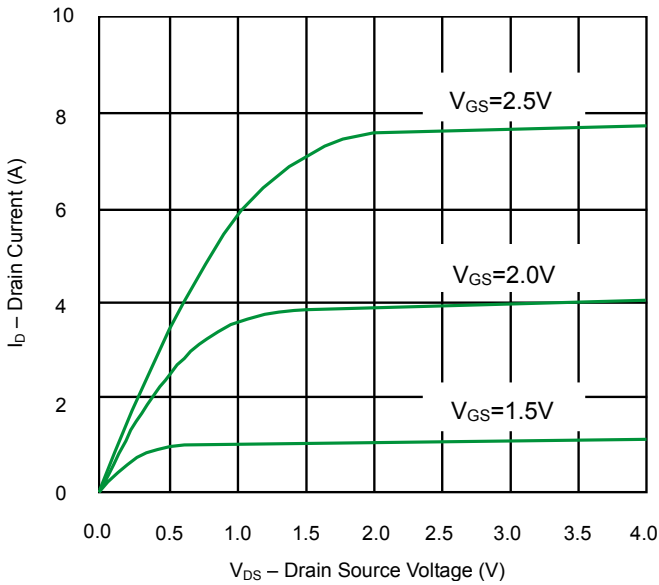


Fig 1. Output Characteristics

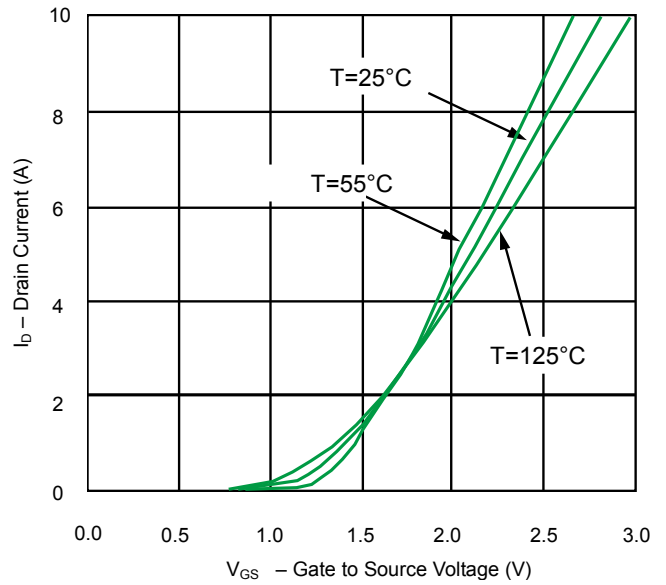


Fig 2. Transfer Characteristics

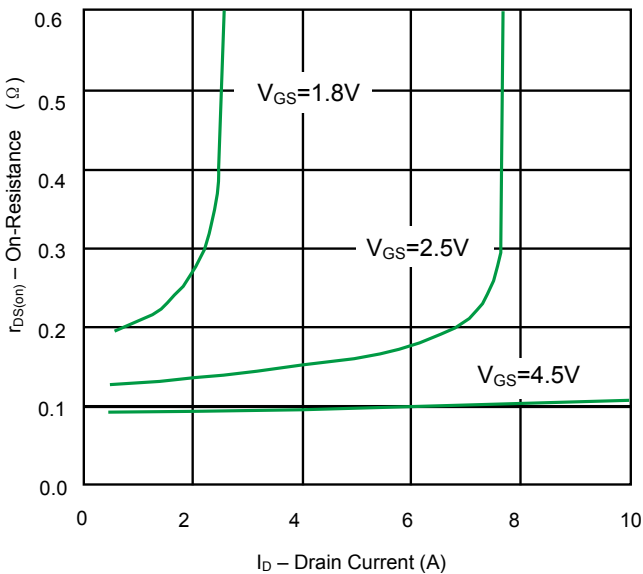


Fig 3. On-Resistance vs. Drain Current

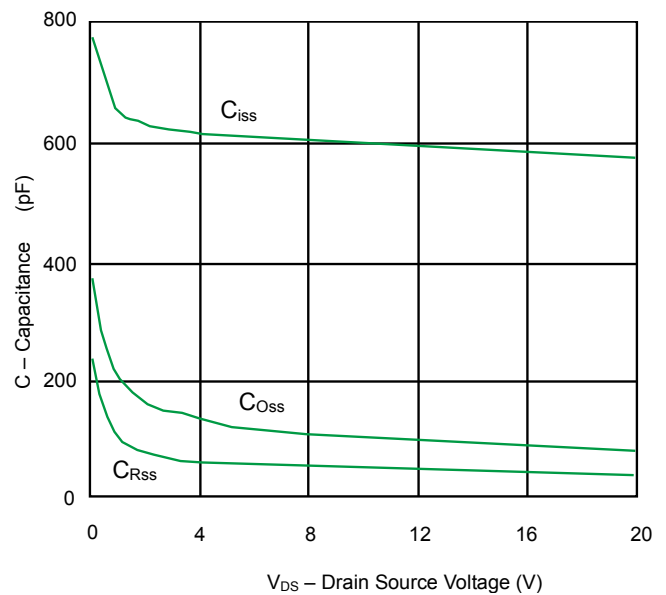
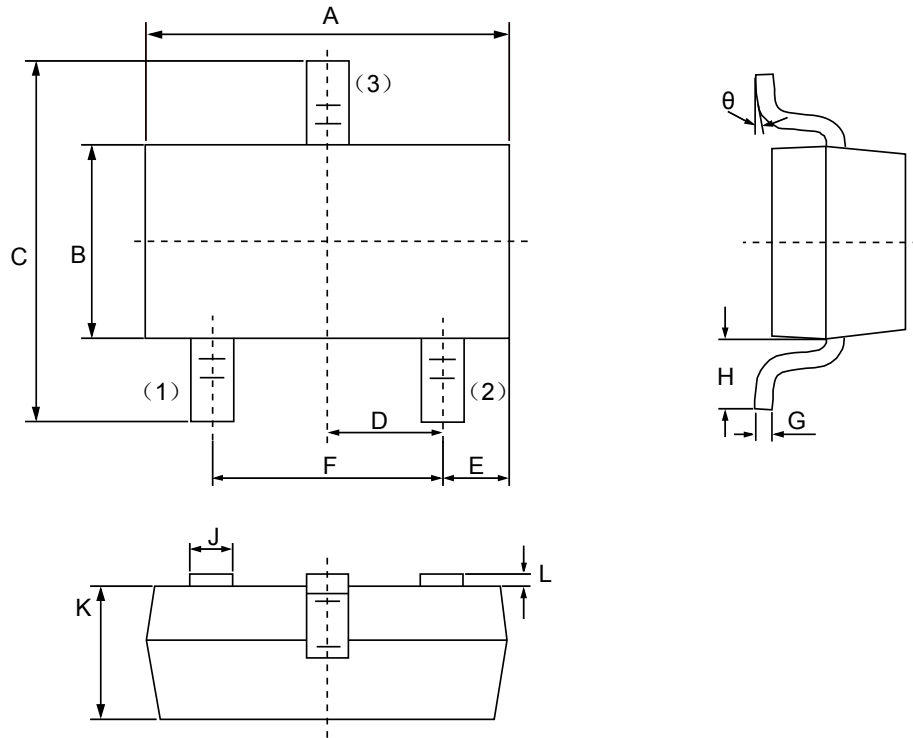



Fig 4. Capacitance

Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°


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